

7.22-98 7.20-98

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT application of:)	
Shunpei YAMAZAKI et al.)	Examiner: S. Crane
Serial No. 08/183,800)	Art Unit: 2508
Filed: January 21, 1994)	
For: SEMICONDUCTOR MATERIAL)	
AND METHOD FOR FORMING)	
THE SAME AND THIN FILM)	
TRANSISTOR)	June 26, 1998

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231, on June 26, 1998.

Ingeborg S. Alexander

INFORMATION DISCLOSURE STATEMENT

Honorable Assistant Commissioner for Patents Washington, D.C. 20231

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In accordance with the provisions of 37 C.F.R. 1.56 and 37 C.F.R. 1.97-1.99, it is requested that the reference(s) listed on the attached Form PTO-1449 be made of record in the above-identified application.

Recently issued U.S. Patent 5,744,818 is relevant to the claimed Raman shift.

The remainder of the references were cited in related applications Serial No. 08/095,172 and 08/428,842 (now, U.S. Patent No. 5,744,818).

Finally, the Examiner's attention is directed to the abstract and Column 7, lines 58-65 of Prior Art U.S. Patent 5,543,636 (cited in an Information Disclosure Statement on March 14, 1997), which discloses concentrations of oxygen, nitrogen, or carbon of 5x10¹⁸ atoms/cm³ or less.

A copy of the references is submitted herewith in accordance with 37 C.F.R. 1.98(a). The requisite fee of \$240 is also submitted herewith in accordance with 37 C.F.R. 1.97(c).

Respectfully submitted,

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